



# Large area micromegas detector for AMBER: lateral module test

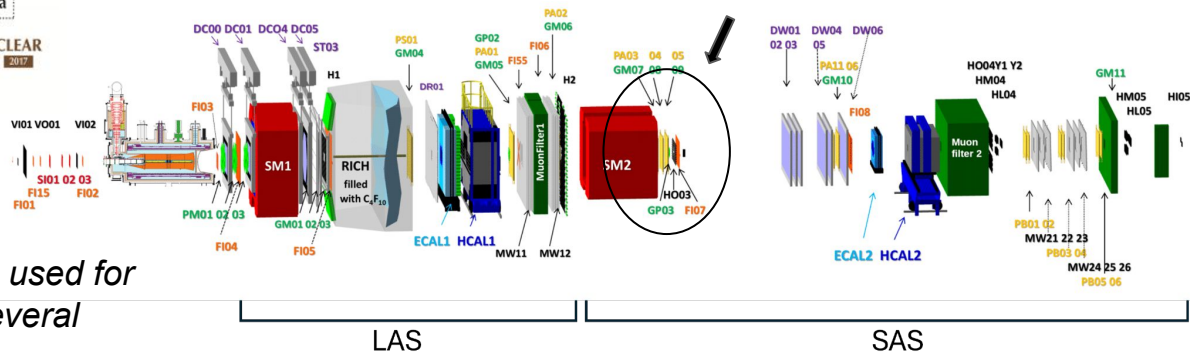
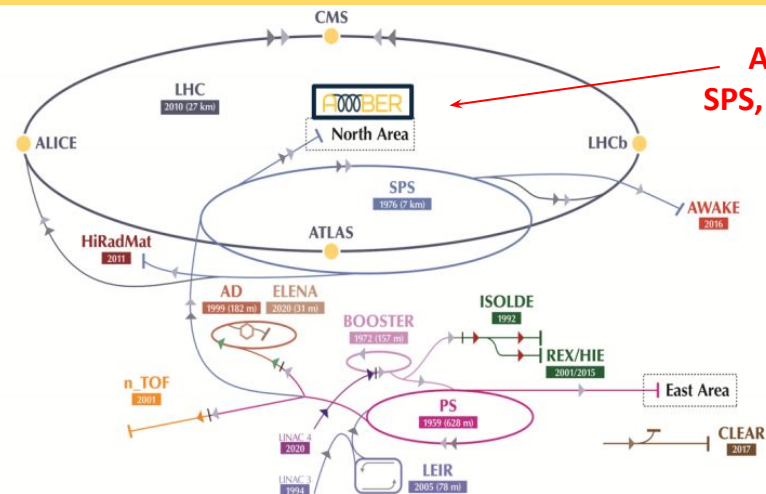
Chiara Alice

on behalf of AMBER-micromegas group  
University of Torino  
INFN Torino  
CERN

# AMBER experiment at CERN

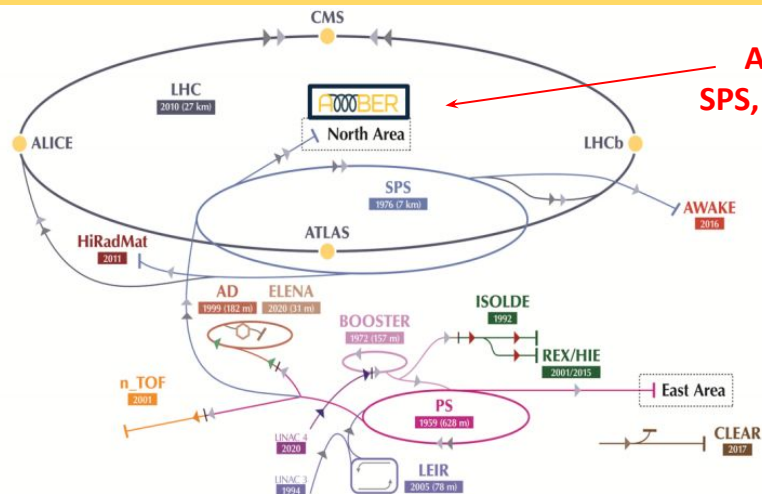
**AMBER experiment:  
SPS, North area, EHN2 hall**

*AMBER (NA66) is a fixed target experiment at the M2 beam-line in the North Area of CERN. It is located in the same experimental hall (EHN2) in which COMPASS experiment was.*



*The former COMPASS spectrometer is being used for the first phase of AMBER and will undergo several upgrades for the mid- and long-term program.*

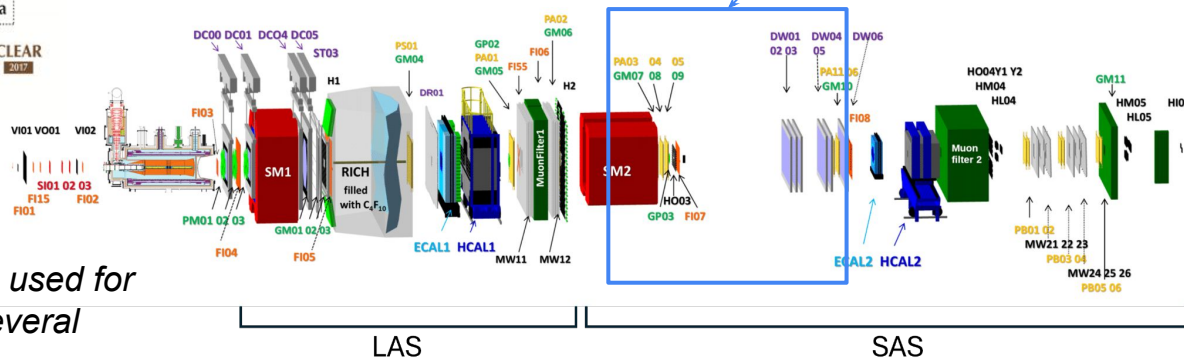
# AMBER experiment at CERN



**AMBER experiment:**  
SPS, North area, EHN2 hall

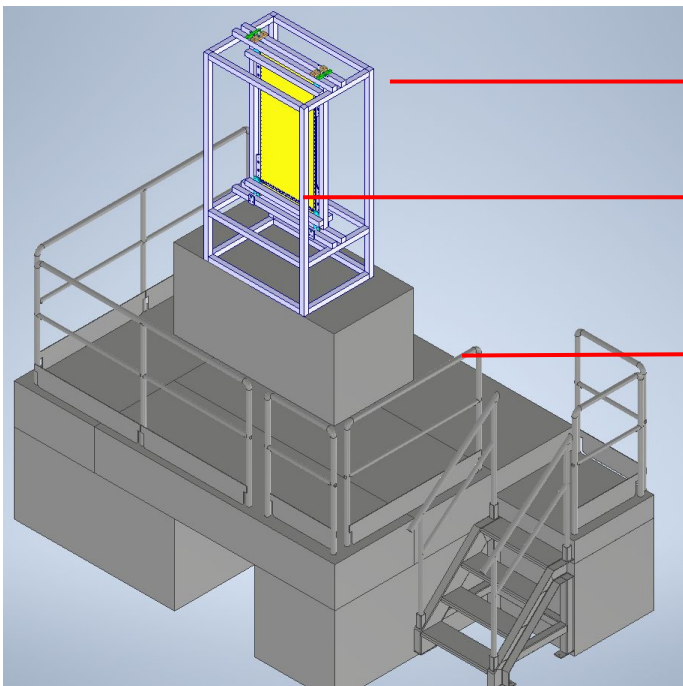
Test area  
downstream SM2

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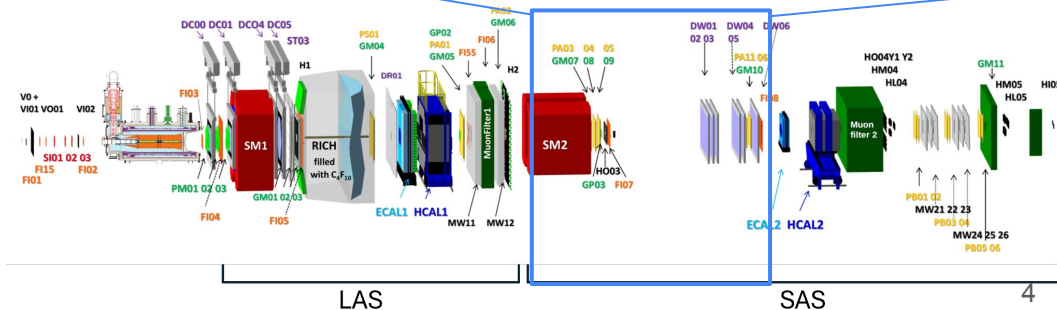
# Test setup @AMBER



Detector holding structure made out of bosch profiles

Micromegas detector lateral module

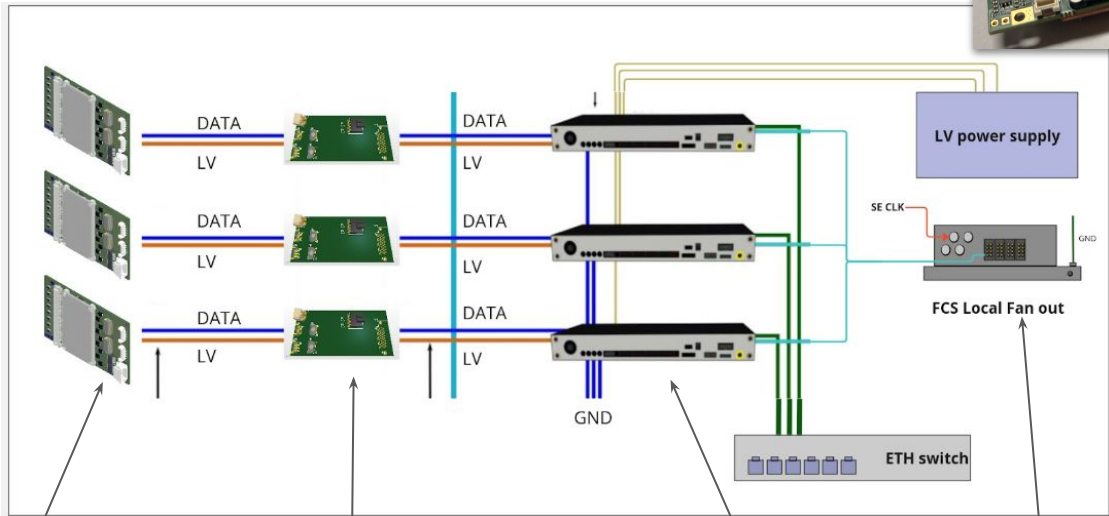
Concrete platform





# Micromegas detector development: tests setup

## AMBER TIGER-based readout chain:



**AMBER-micromegas\_FE**  
designed at INFN To

**Data and Low Voltage Patch Card - DLVPC**  
designed at JINR

**GEMROC modules**  
designed at INFN Fe

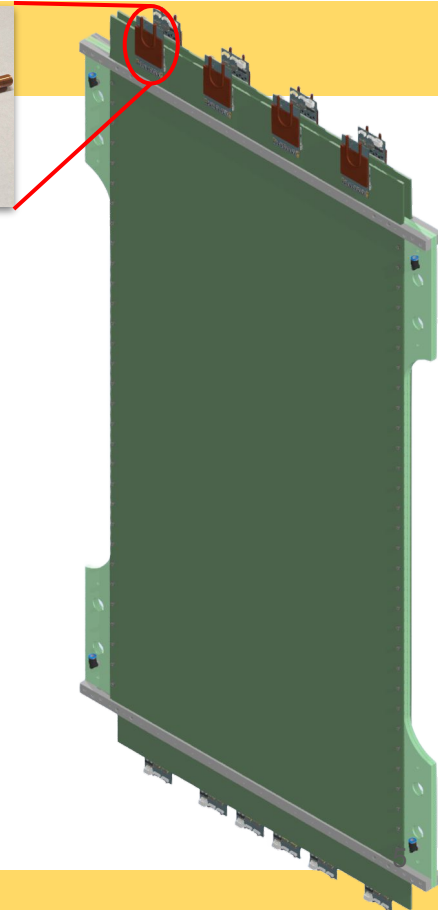
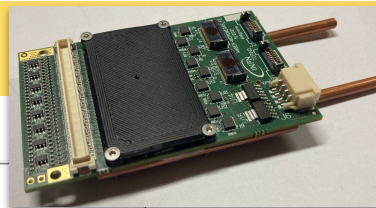
**Local FAN OUT**  
designed at INFN Fe

TIGER-based front-end board

adapter for data and LV

Configuration and control  
signal distribution  
Data concentration

Trigger and clock  
distribution



# Backup slides

## MM stackup

material	Density [g/cm <sup>3</sup> ]
Cu	8.96
Glass epoxy	1.98
Prepreg	1.47
Kapton	1.42
photoresist	1
DLC	3
Stainless steel	7.93

X shielding and connector layer : 35um copper

-3.2mm Glass epoxy  
 X strip layer : 35um Copper  
 -50um Prepreg  
 -50um Kapton  
 X DLC layer  
 -pillars 150um  
 X mesh: 45/18

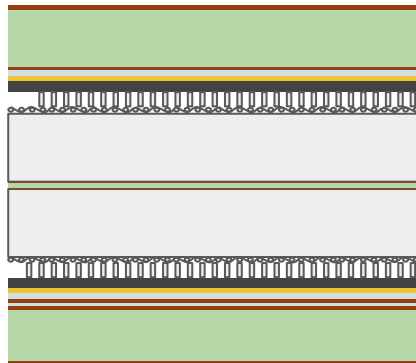
Drift gap : 5mm

Drift mesh : 45/18

Drift gap: 5mm

U.V mesh: 45/18  
 -pillars 150um  
 U.V DLC layer  
 -50um Kapton  
 -50um Prepreg  
 U layer: 35um Copper  
 -28um Prepreg  
 V Layer: 17um copper  
 -3.2mm glass epoxy

U.V bottom shielding and connector layer: 35um copper



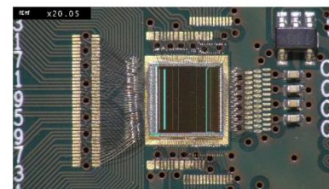
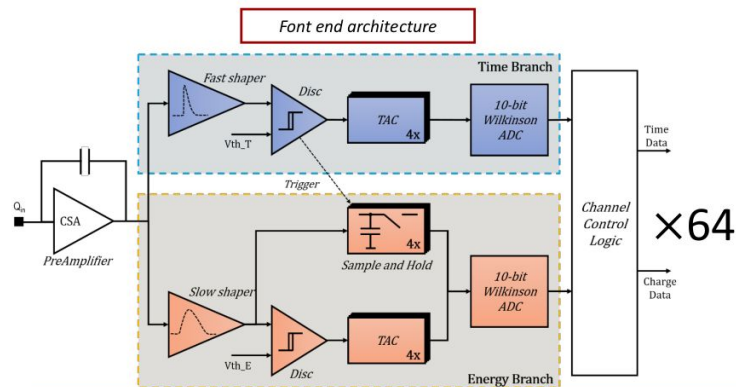
- Cu:
  - SHIELDING x2:**  $(0.0035 \times 100 \times 51.2) \times 2 \text{ cm}^3 = 17.92 \times 2 \text{ cm}^3$
  - X strips:**  $(0.0035 \times 100 \times 25.6) \text{ cm}^3 = 8.96 \text{ cm}^3$
  - U strips:**  $(0.0035 \times 100 \times 32) \text{ cm}^3 = 11.2 \text{ cm}^3$
  - V strips:**  $(0.0035 \times 100 \times 32) \text{ cm}^3 = 11.2 \text{ cm}^3$
  - Total copper = 602.112 g
- Glass epoxy:
  - x2**  $(0.32 \times 100 \times 51.2) \times 2 \text{ cm}^3 = 1638 \times 2 \text{ cm}^3$
  - Total glass epoxy = 6486.5 g
- Prepreg:
  - x2**  $(0.005 \times 100 \times 51.2) \times 2 \text{ cm}^3 = 25.6 \times 2 \text{ cm}^3$  ;
  - x1**  $(0.0028 \times 100 \times 51.2) \text{ cm}^3 = 14.336 \text{ cm}^3$
  - Total Prepreg : 96.338 g
- Kapton:
  - x2**  $(0.005 \times 100 \times 51.2) \times 2 \text{ cm}^3 = 25.6 \times 2 \text{ cm}^3$
  - Total Kapton: 72.704 g
- Photoresist (uniform layer approx):
  - x2**  $(0.0150 \times 100 \times 51.2) \times 2 \text{ cm}^3 = 65.536 \times 2 \text{ cm}^3$
  - Total photoresist: 127,072 g
- DLC:
  - x2**  $(0.01 \times 100 \times 51.2) \times 2 \text{ cm}^3 = 51.2 \times 2 \text{ cm}^3$
  - Total DLC: 307.2 g
- Stainless Steel (uniform layer approx):
  - x3**  $(0.0018 \times 100 \times 51.2) \times 3 \text{ cm}^3 = 9.216 \times 3 \text{ cm}^3$
  - Total SS: 219.25 g

**Total mass first estimation: 7.912 kg**

## Backup slides

# TIGER ASIC

Torino Integrated Gem Electronics Readout



TIGER bonded on PCB



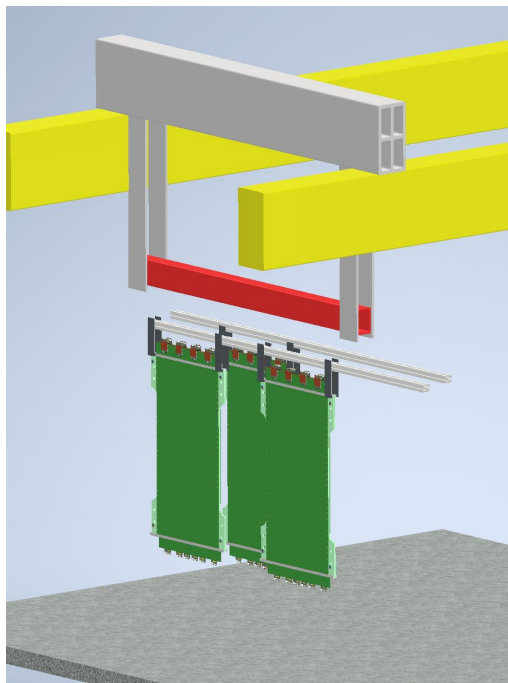
Front end board (FEB)

### Chip features:

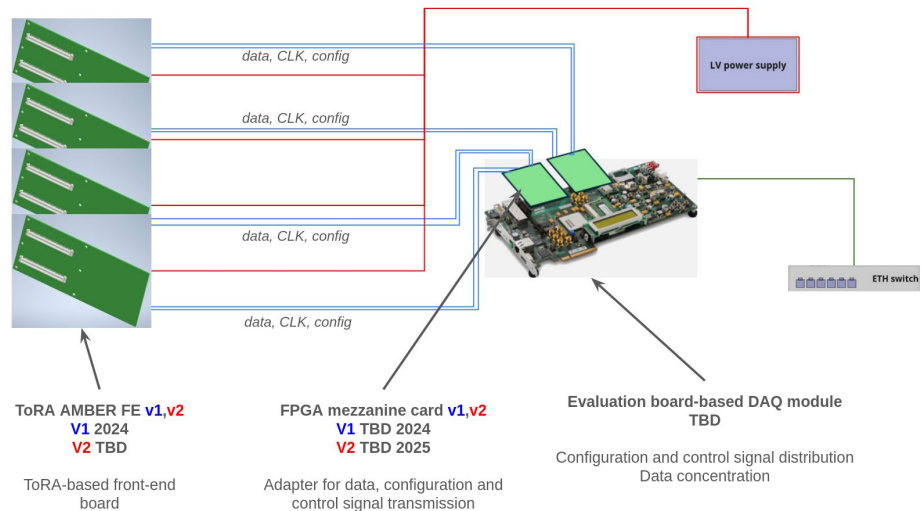
- 64 channels
- Power consumption < 12 mW/channel
- Sustained event rate 100 kHz
- Input dynamic range up to 50 fC
- Time resolution < 5 ns
- ENC < 2000 e<sup>-</sup> rms with 100 pF input capacitance
- Analog read out providing charge and time measurement
- Digital logic protected from single event upset (SEU)
- Tunable internal test pulse generator
- 110 nm technology

## Backup slides: DY test run

*For Drell-Yan test run (2025) definitive suspension structure + FEE should be finalized:*



### AMBER ToRA-based readout chain



*DAQ still not defined, we are at the stage of stand-alone readout chain design. AMBER integration to be defined.*